Comments and Corrections

Correction to "A Linearized, Low Phase Noise VCO Based 25 GHz PLL With Autonomic Biasing"

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The authors had used a different variable, t_B, for the bias tuning knob in equation (3) as compared to $V_{\mathrm{g,bias}}$ in the rest of the paper. Using the consistent variable, $V_{\mathrm{g,bias}}$, for the bias tuning knob, the equation is revised to:

$$L\{\Delta f\} = f(A, I, f_0, k_B, V_{\mathrm{g,bias}}) \tag{3}$$

where $f(\bullet)$ is a polynomial function, A is the carrier amplitude, I is the VCO current, f_0 is the oscillation frequency, k_B is the frequency tuning knob, and $V_{\mathrm{g,bias}}$ is the bias tuning knob.

References

[1] B. Sadhu, M. Ferriss, A. Natarajan, S. Yaldiz, J.-O. Plouchart, A. Rylyakov, A. Valdes-Garcia, B. Parker, A. Babakhani, S. Reynolds, X. Li, L. Pileggi, R. Harjani, J. Tierno, and D. Friedman, "A linearized, low-phase-noise VCO-based 25-GHz PLL with autonomic biasing," *IEEE J. Solid-State Circuits*, vol. 48, no. 5, pp. 1138–1150, May 2013.

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Correction to "A 0.016 mm² 144-µW Three-Stage Amplifier Capable of Driving 1-to-15 nF Capacitive Load With >0.95-MHz GBW"

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In the above paper [1], the Patent [2] was cited in the description of Fig. 8, for a more general description about the utilization and advantages of the G_{ma} stage. However, [3] exhibits the circuit implementation of the G_{ma} stage (improved Ahuja compensation circuit), which, for that reason, should have been referenced for completeness, as well. The authors would like to thank Dr. U. Dasgupta for pointing out this missing information.

References

[1] Z. Yan *et al.*, "A 0.016 mm^2 144- μW three-stage amplifier capable of driving 1-to-15 nF capacitive load with $>$0.95-MHz GBW," *IEEE J. Solid-State Circuits*, vol. 48, no. 2, pp. 527–540, Feb. 2013.

[2] U. Dasgupta, "Ahuja Compensation Circuit for Operational Amplifiers," U.S. patent 7,646,247, Jan. 12, 2010.

[3] U. Dasgupta, "Issues in "Ahuja" frequency compensation technique," in *Proc. IEEE Int. Symp. Radio-Frequency Integration Technology*, 2009, pp. 326–329.

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